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INFORMATION DISCLOSURE
CITATION

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SE

Unknown

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APPLICANT

IONESCU et al

(Use several sheets if necessary)

FILING DATE


GROUP

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[initials]</i>	4,906,586	3/1990	Blackburn	438	53	
<i>[initials]</i>	5,262,000	11/1993	Welbourn et al	156	643	
<i>[initials]</i>	6,290,864	9/2001	Patel et al	216	79	

FOREIGN PATENT DOCUMENTS

						TRANSLATION	
DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO	
 WO 99/26333	5/1999	WIPO					

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

<i>[initials]</i>	Ionescu et al, "Modeling and Design of a Low-Voltage SOI Suspended-Gate MOSFET (SG-MOSFET) with a Metal-Over-Gate Architecture", PROCEEDINGS OF THE 2002 3 RD INTERNATIONAL SYMPOSIUM ON QUALITY ELECTRONIC DESIGN, March 18-21, 2002, pp. 496-501.
	Hoffman et al, "3D Structures with Piezoresistive Sensors in Standard CMOS", PROCEEDINGS OF THE WORKSHOP ON MICRO ELECTRICAL MECHANICAL SYSTEMS, January 29 - February 2, 1995, pp. 288-293.
	Devoe et al, "Surface Micromachined Piezoelectric Accelerometers (PIXLS)", JOURNAL OF MICROELECTROMECHANICAL SYSTEMS, IEEE INC., vol. 10, no. 2, June 2001, pp. 180-186.
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<i>[initials]</i>	Meister et al, "In situ control of the electrochemical gap height modification of a suspended gate field-effect transistor by capacitance -- voltage measurement technique", SENSORS AND ACTUATORS B, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. 46, no. 3, 15 May 1998, pp. 226-235.

*Examiner

Date Considered

7/10/06

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